2SA 1266
2SA 1266 Ⓛ

SILICON PNP TRANSISTOR
EPITAXIAL PLANAR TYPE (PCT PROCESS)

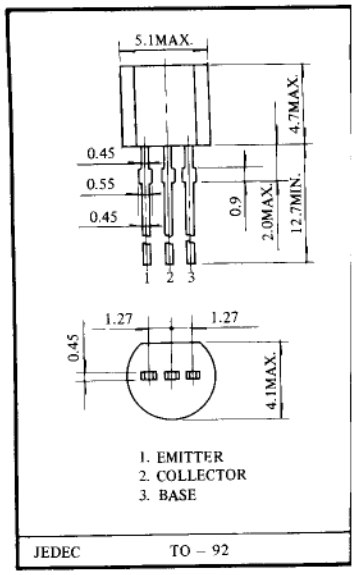
APPLICATIONS

- Low Frequency Amplifier
- Low Noise Amplifier

FEATURES

- Excellent h_{FE} Linearity, $h_{FE}(0.1mA)/h_{FE}(2mA)=0.95$ (Typ.)
- Excellent Safe Operation Area
- Low Noise 2SA1266 NF=1dB (TYP), 10dB (Max.)
  2SA1266Ⓛ NF=0.2dB (TYP), 3dB (Max.)
- Complementary to the 2SC3198/2SC3198Ⓛ

Unit in mm



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC TO-92

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	−50	V
Collector-Emitter Voltage	V_{CEO}	−50	V
Emitter-Base Voltage	V_{EBO}	−5	V
Collector Current	I_C	−150	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Emitter Current	I_E	150	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	125	℃
Storage Temperature Range	T_{stg}	−55~125	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut off Current		I_{CBO}	$V_{CB}=-50V$, $I_E=0$	-	-	−0.1	μA
Emitter Cut off Current		I_{EBO}	$V_{EB}=-5V$, I_C	-	-	−0.1	μA
DC Current Gain (1)		$h_{FE(1)}$	$V_{CE}=-6V$, $I_C=-2mA$	70	-	400	-
DC Current Gain (2)		$h_{FE(2)}$	$V_{CE}=-6V$, $I_C=-150mA$	25	-	-	-
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=-100mA$, $I_B=-10mA$	-	−0.1	−0.3	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C=-100mA$, $I_B=-10mA$	-	-	−1.1	V
Transition Frequency		f_T	$V_{CE}=-10V$, $I_E=1mA$	80	-	-	MHz
Output Capacitance		C_{ob}	$V_{CB}=-10V$, $I_C=0$, f=1MHz	-	4	7	pF
Base Spreading Resistance		$r_{bb'}$	$V_{CB}=-10V$, $I_C=-1mA$, f=30MHz	-	30	-	Ω
Noise Figure	2SA1266	NF	$V_{CE}=-6V$, $I_C=0.1mA$	-	1.0	10	dB
	2SA1266Ⓛ		Rg=10kΩ, f=1KHz	-	0.2	3	

NOTE: According to h_{FE} (1), Classified as follows

O	70-140	Y	120~240	GR	200~400